

**N- Channel Enhancement mode MOSFET AND Schottky Diode**

# MTB1K6N06KS6R

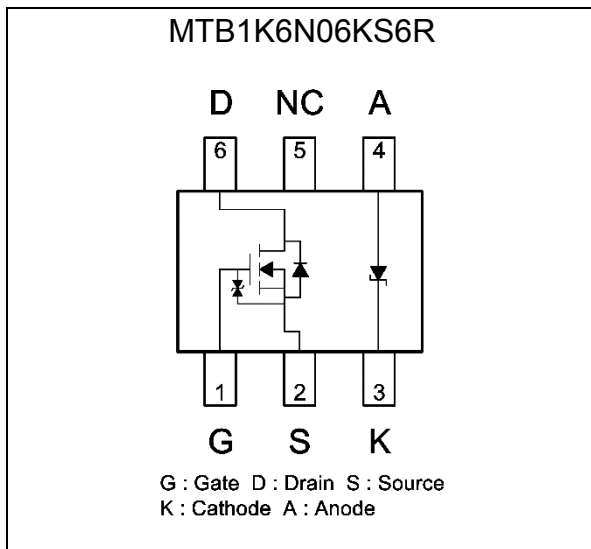
**Features**

- N-MOS with ESD Gate Protection
- N-MOS with Low On-Resistance
- Low  $V_F$  Schottky Diode
- Low Static, Switching and Conduction Losses

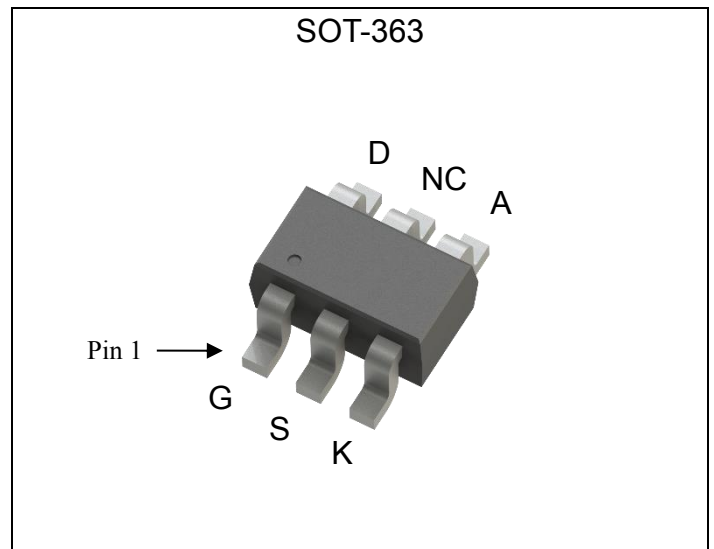
$BV_{DSS}$	60V
$I_D @ V_{GS}=10V, T_A=25^\circ C$	0.25A
$R_{DS(ON) typ.} @ V_{GS}=10V, I_D=0.1A$	1.1 $\Omega$
$R_{DS(ON) typ.} @ V_{GS}=4.5V, I_D=0.1A$	1.2 $\Omega$

$V_{RRM}$	40V
$I_O$	1A

**Equivalent Circuit**

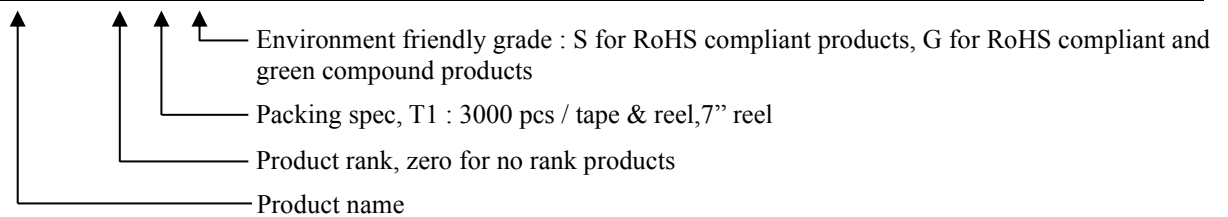


**Outline**



**Ordering Information**

Device	Package	Shipping
MTB1K6N06KS6R-0-T1-G	SOT-363 (Pb-free lead plating and halogen-free package)	3000 pcs / Tape & Reel





**Absolute Maximum Ratings (T<sub>A</sub>=25°C)**

**NMOS**

Parameter	Symbol	Limits	Unit
Drain-Source Voltage	V <sub>DS</sub>	60	V
Gate-Source Voltage	V <sub>GS</sub>	±20	
Continuous Drain Current @ V <sub>GS</sub> =10V, T <sub>A</sub> =25°C	I <sub>D</sub>	0.25	A
Continuous Drain Current @ V <sub>GS</sub> =10V, T <sub>A</sub> =70°C		0.20	
Pulsed Drain Current *a	I <sub>DM</sub>	1	
Continuous Body Diode Forward Current @ T <sub>A</sub> =25°C	I <sub>S</sub>	0.25	
ESD susceptibility *b	V <sub>ESD</sub>	2000	V
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55~+150	°C

**Schottky Diode**

Parameter	Symbol	Limits	Unit
Repetitive peak reverse voltage	V <sub>RRM</sub>	40	V
Maximum RMS voltage	V <sub>RMS</sub>	28	
Maximum DC blocking voltage	V <sub>R</sub>	40	
Maximum instantaneous forward voltage, I <sub>F</sub> =1A (Note 1)	V <sub>F</sub>	0.55	A
Average forward rectified current	I <sub>O</sub>	1	
Peak forward surge current @8.3ms single half sine wave superimposed on rated load (JEDEC method)	I <sub>FSM</sub>	4	A
Maximum DC reverse current V <sub>R</sub> =40V, T <sub>J</sub> =25°C (Note 1) V <sub>R</sub> =40V, T <sub>J</sub> =125°C (Note 1)	I <sub>R</sub>	0.3	mA
		10	mA
Diode junction capacitance @ f=1MHz and applied 5V reverse voltage	C <sub>D</sub>	55 (typ)	pF
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55~+150	°C

**Thermal Data**

Parameter	Symbol	Steady State	Unit
Total Power Dissipation	P <sub>D</sub>	300	mW
Thermal Resistance, Junction-to-ambient	R <sub>θJA</sub>	500	°C/W

Note:

\*a. Repetitive rating, pulse width limited by junction temperature T<sub>J(MAX)</sub>=150°C. Ratings are based on low frequency and low duty cycles to keep initial T<sub>J</sub>=25°C.

\*b. Human body model, 1.5kΩ in series with 100pF.



**N-Channel MOSFET Electrical Characteristics (T<sub>A</sub>=25°C, unless otherwise specified)**

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
<b>Static</b>					
BV <sub>DSS</sub>	60	-	-	V	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA
V <sub>GS(th)</sub>	1	-	2.5		V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA
G <sub>FS</sub>	-	0.25	-	S	V <sub>DS</sub> =10V, I <sub>D</sub> =0.1A
I <sub>GSS</sub>	-	-	±10	μA	V <sub>GS</sub> =±16V, V <sub>DS</sub> =0V
I <sub>DSS</sub>	-	-	1		V <sub>DS</sub> =48V, V <sub>GS</sub> =0V
R <sub>DS(ON)</sub>	-	1.1	2	Ω	V <sub>GS</sub> =10V, I <sub>D</sub> =0.1A
	-	1.2	3		V <sub>GS</sub> =4.5V, I <sub>D</sub> =0.1A
<b>Dynamic</b>					
C <sub>iss</sub>	-	25	-	pF	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V, f=1MHz
C <sub>oss</sub>	-	9	-		
C <sub>rss</sub>	-	7	-		
Q <sub>g</sub> *1, 2	-	0.75	-	nC	V <sub>DS</sub> =30V, I <sub>D</sub> =0.1A, V <sub>GS</sub> =4.5V
Q <sub>g</sub> *1, 2	-	1.5	-		
Q <sub>gs</sub> *1, 2	-	0.45	-		
Q <sub>gd</sub> *1, 2	-	0.15	-		
t <sub>d(ON)</sub> *1, 2	-	4	-	ns	V <sub>DS</sub> =30V, I <sub>D</sub> =0.2A, V <sub>GS</sub> =10V, R <sub>GS</sub> =1Ω
t <sub>r</sub> *1, 2	-	15	-		
t <sub>d(OFF)</sub> *1, 2	-	10	-		
t <sub>f</sub> *1, 2	-	16	-		
<b>Source-Drain Diode</b>					
V <sub>SD</sub> *1	-	0.8	1.2	V	I <sub>S</sub> =0.1A, V <sub>GS</sub> =0V
t <sub>rr</sub>	-	9	-	ns	I <sub>F</sub> =0.2A, dI <sub>F</sub> /dt=100A/μs
Q <sub>rr</sub>	-	2.7	-	nC	

Note:

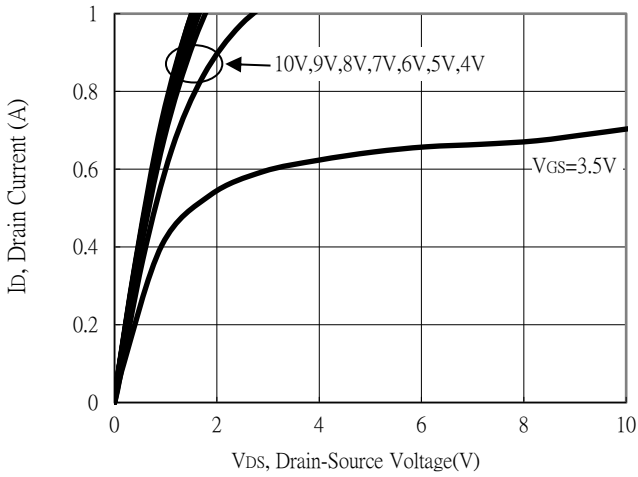
\*1. Pulse Test : Pulse Width ≤300μs, Duty Cycle≤2%

\*2. Independent of operating temperature

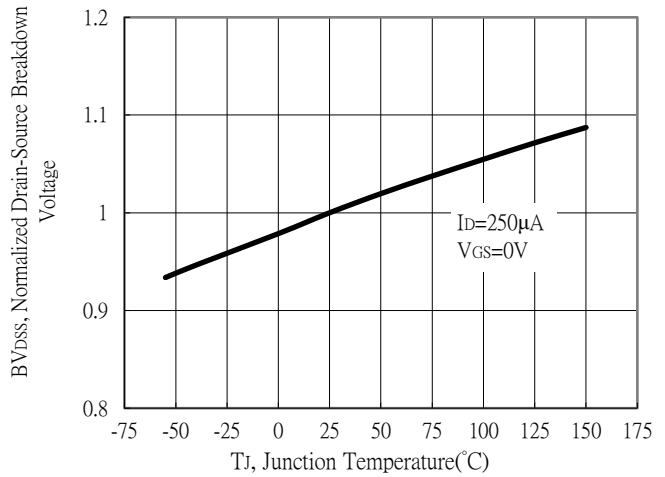


**Typical Characteristics : NMOS**

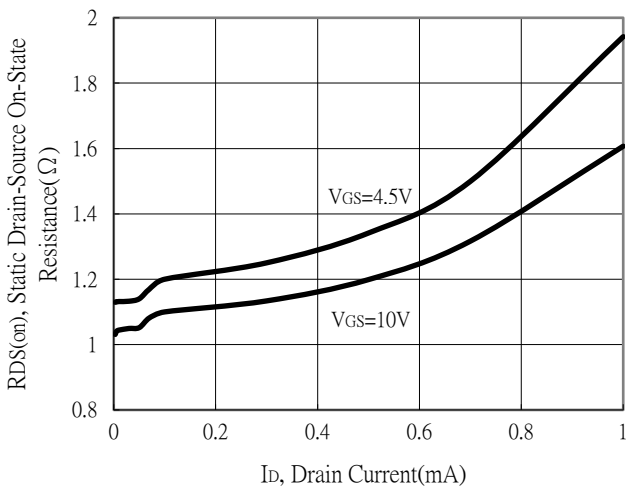
Typical Output Characteristics



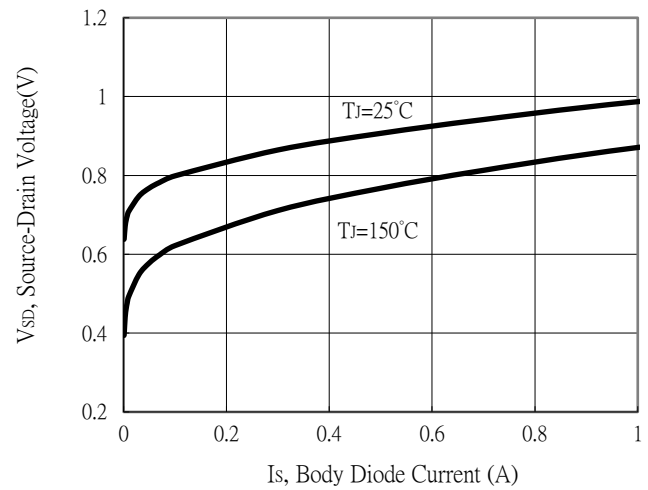
Breakdown Voltage vs Ambient Temperature



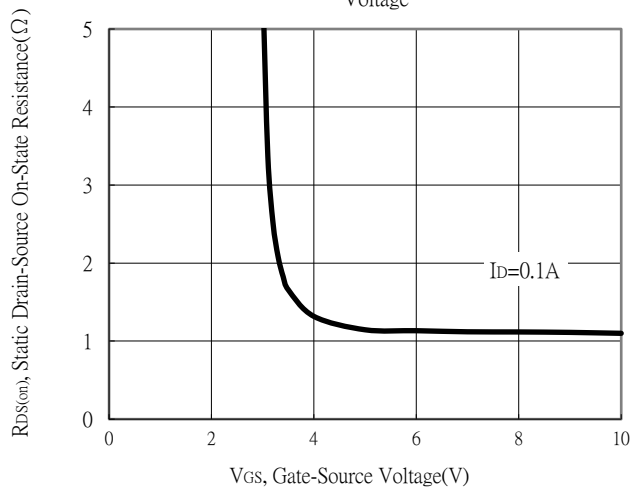
Static Drain-Source On-State resistance vs Drain Current



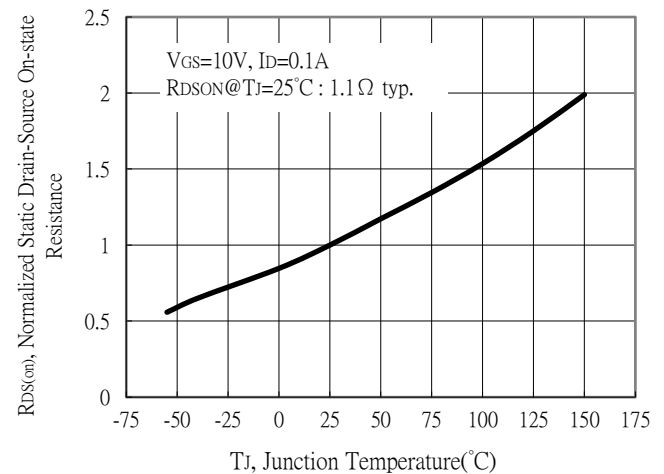
Body Diode Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage



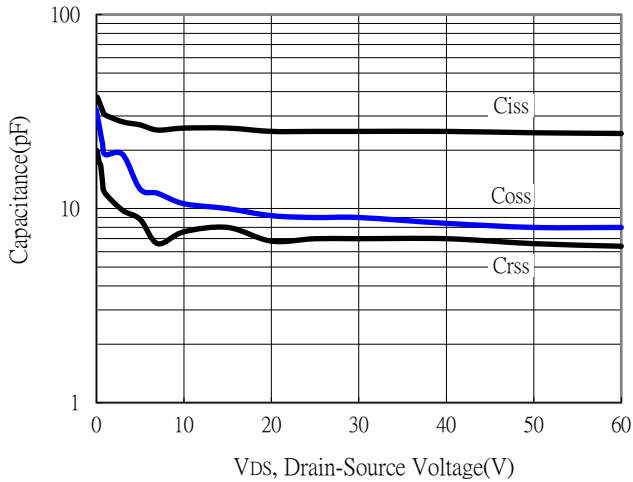
Drain-Source On-State Resistance vs Junction Temperature



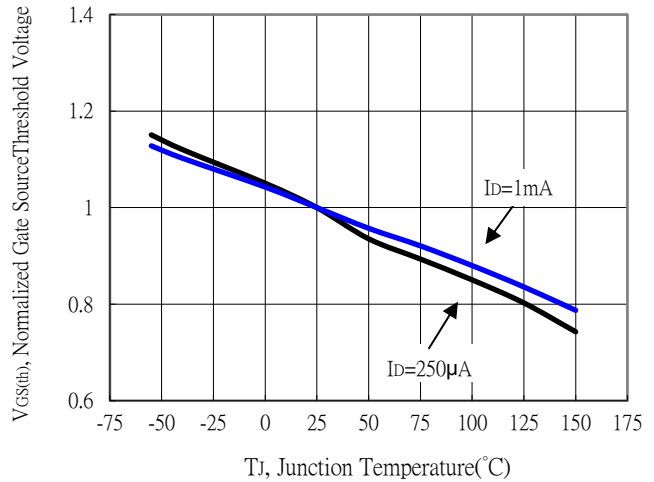


**Typical Characteristics : NMOS (Cont.)**

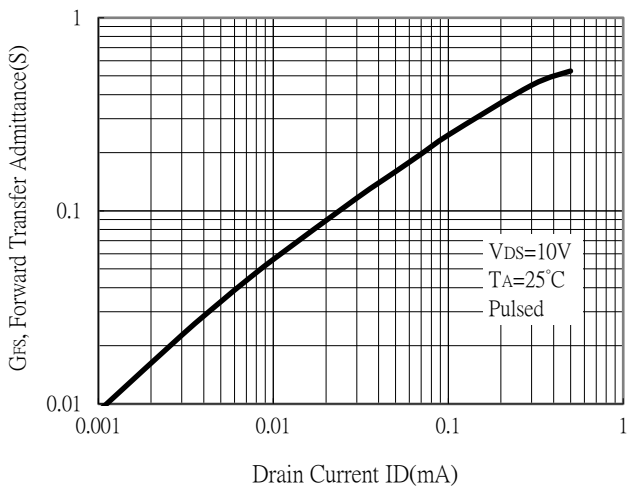
Capacitance vs Drain-to-Source Voltage



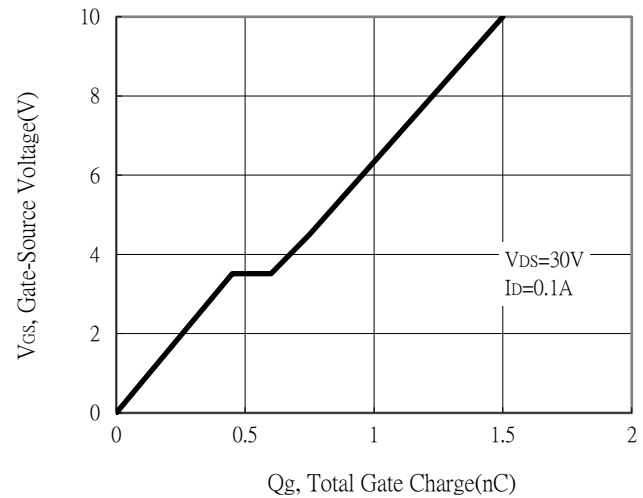
Threshold Voltage vs Junction Temperature



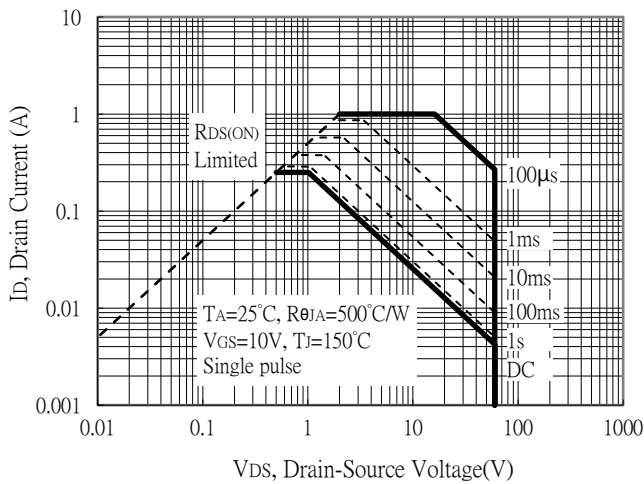
Forward Transfer Admittance vs Drain Current



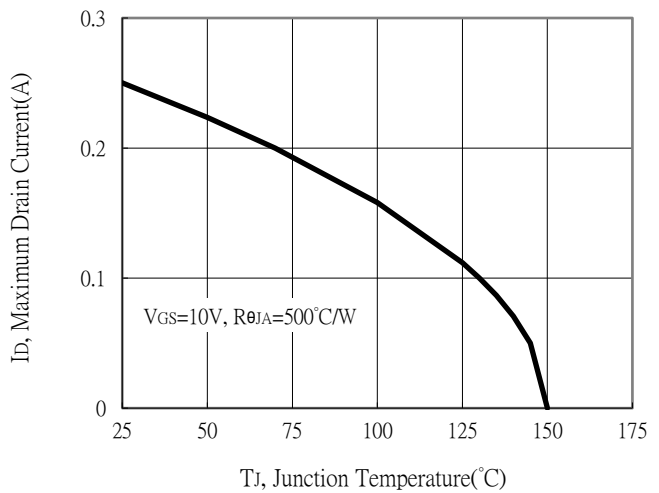
Gate Charge Characteristics



Maximum Safe Operating Area

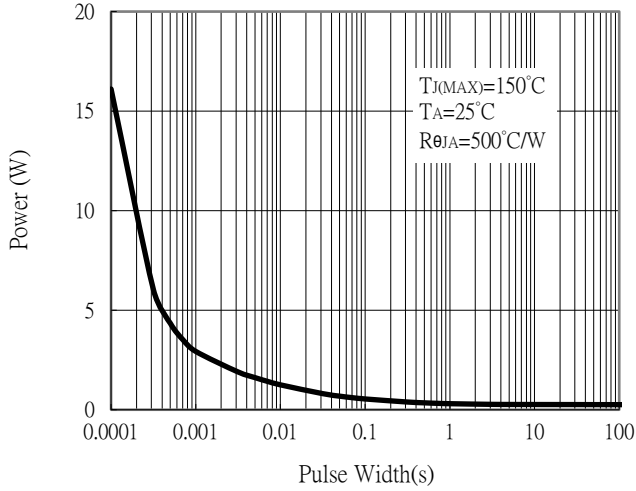


Maximum Drain Current vs Junction Temperature

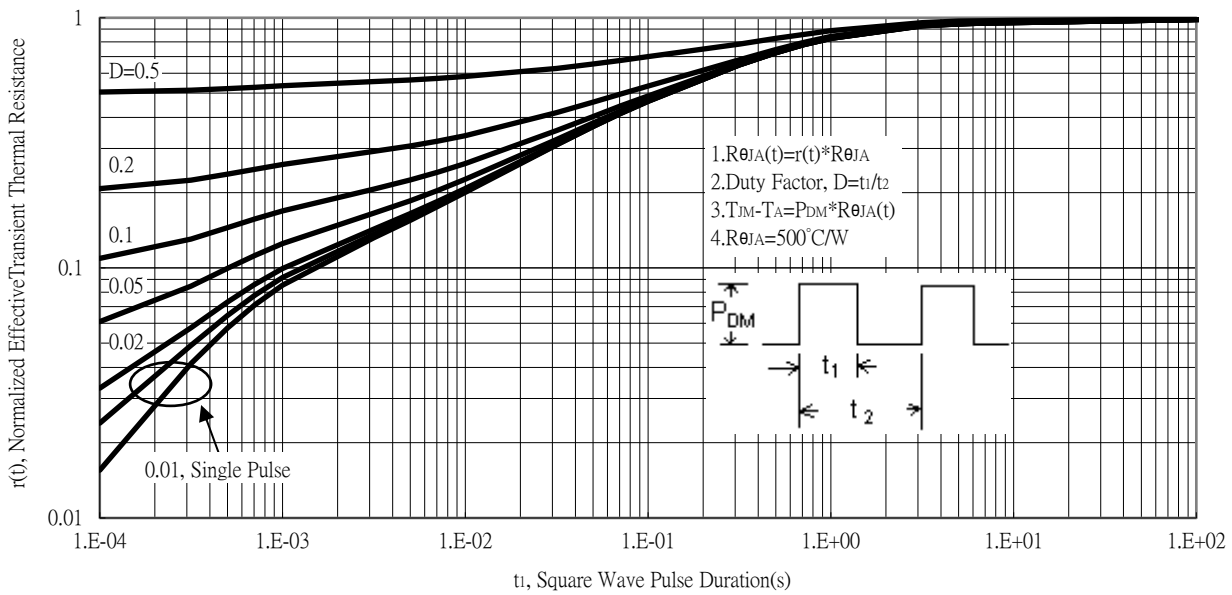


**Typical Characteristics : NMOS (Cont.)**

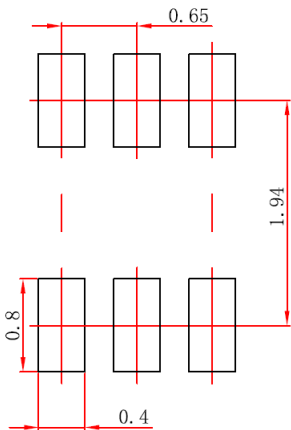
Single Pulse Power Rating, Junction to Ambient



Transient Thermal Response Curves



**Recommended Soldering Footprint**

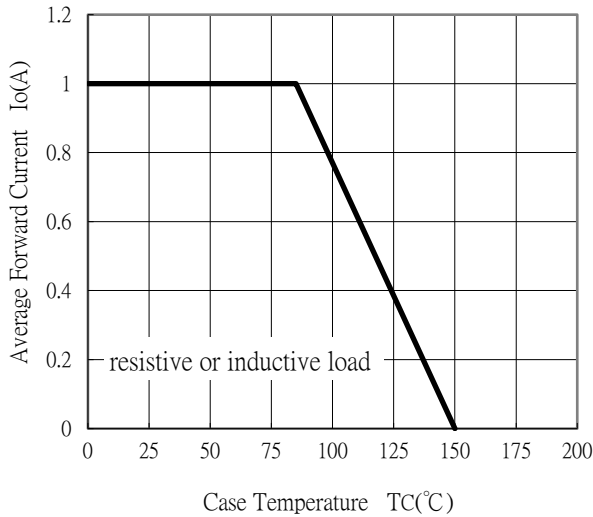


Unit : mm

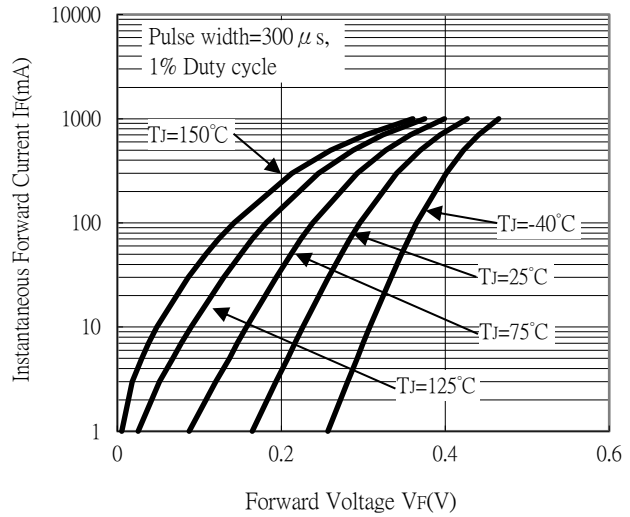


### Typical Characteristics : Schottky Diode

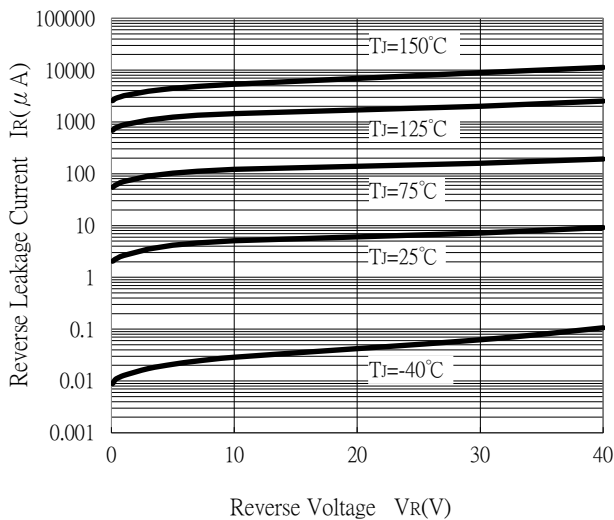
Forward Current Derating Curve



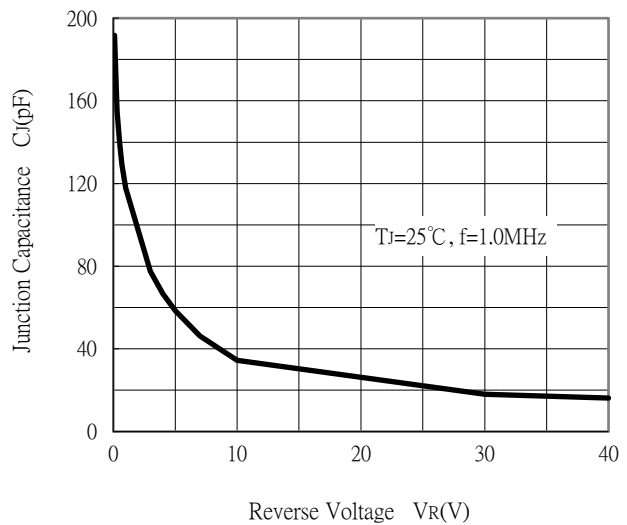
Forward Current vs Forward Voltage



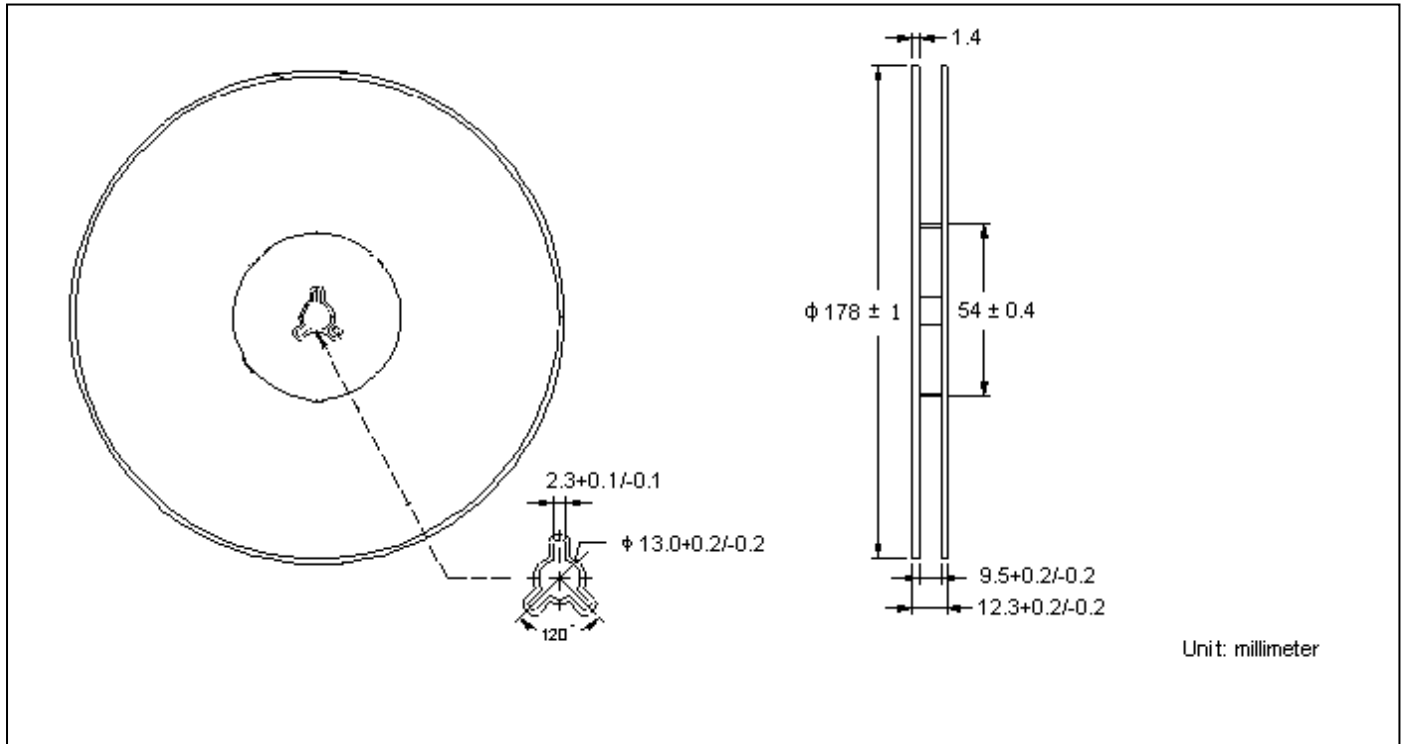
Reverse Leakage Current vs Reverse Voltage



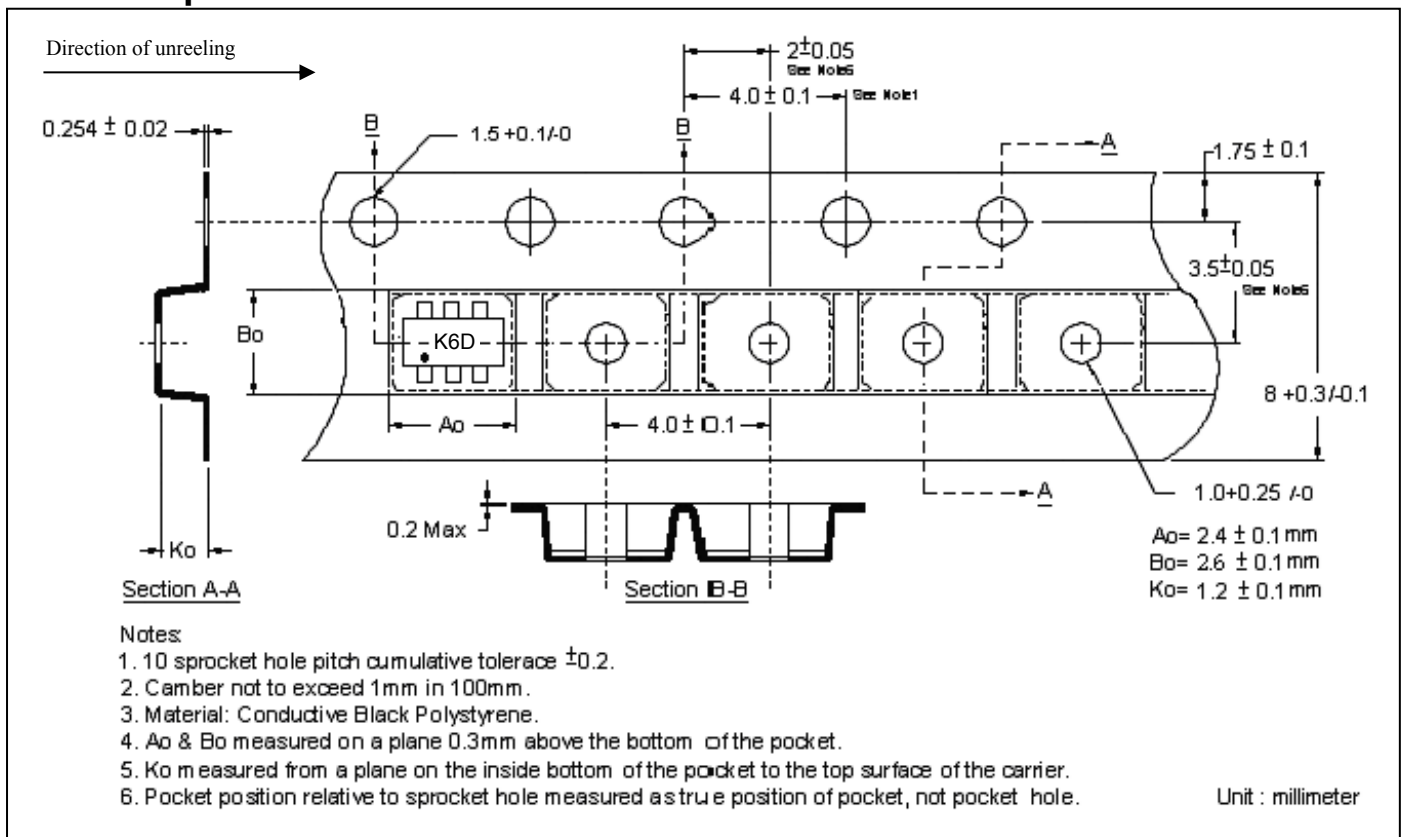
Junction Capacitance vs Reverse Voltage



### Reel Dimension



### Carrier Tape Dimension



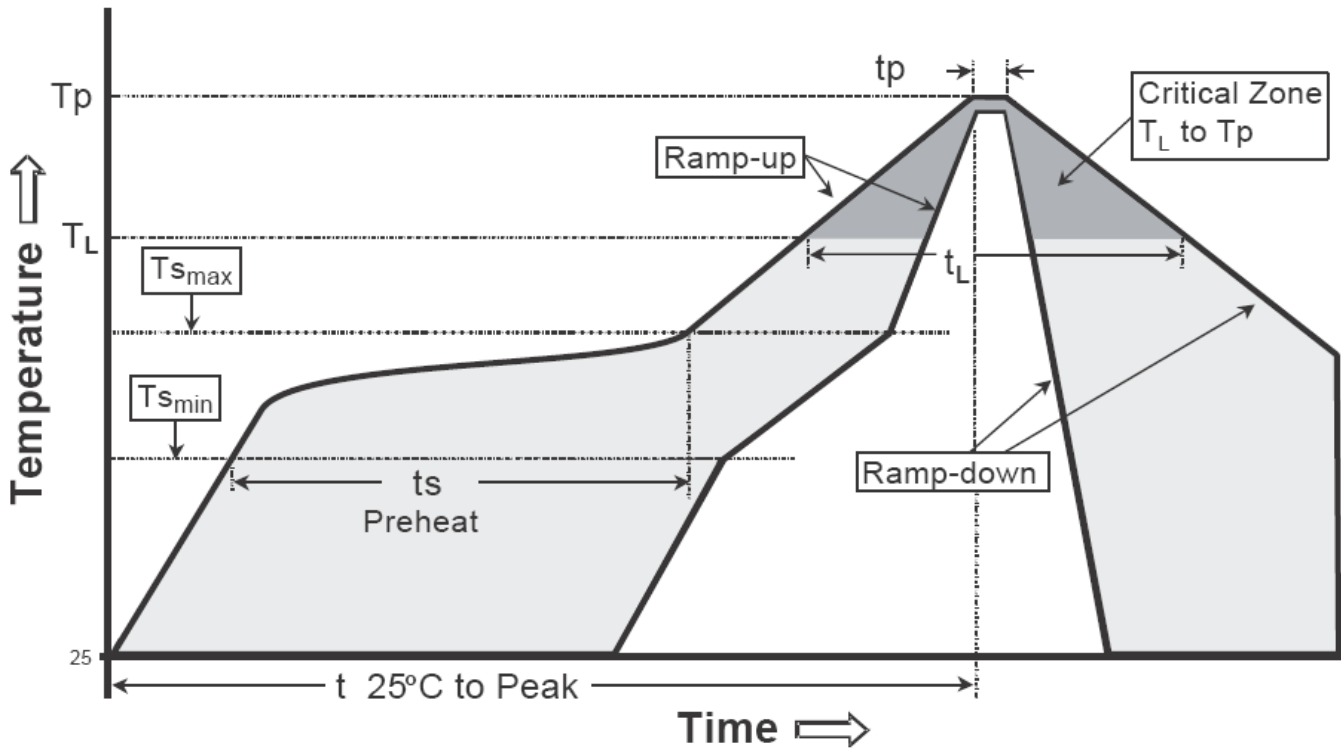




**Recommended wave soldering condition**

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

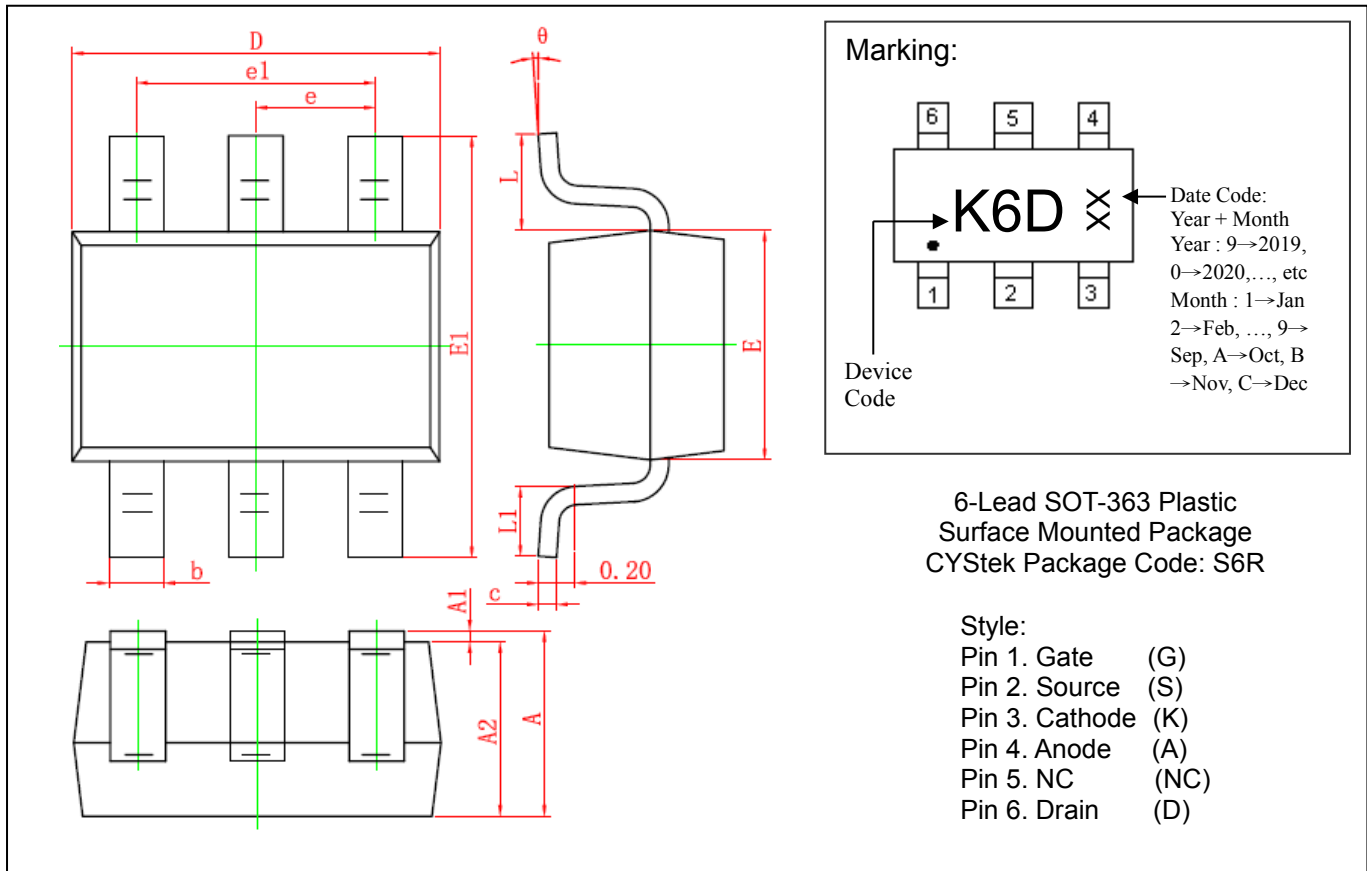
**Recommended temperature profile for IR reflow**



Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (Ts max to Tp)	3°C/second max.	3°C/second max.
Preheat		
-Temperature Min(Ts min)	100°C	150°C
-Temperature Max(Ts max)	150°C	200°C
-Time(ts min to ts max)	60-120 seconds	60-180 seconds
Time maintained above:		
-Temperature (Tl)	183°C	217°C
- Time (tL)	60-150 seconds	60-150 seconds
Peak Temperature(Tp)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

**SOT-363 Dimension**



DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.900	1.100	0.035	0.043	E1	2.150	2.450	0.085	0.096
A1	0.000	0.100	0.000	0.004	e	0.650	TYP	0.026	TYP
A2	0.900	1.000	0.035	0.039	e1	1.200	1.400	0.047	0.055
b	0.150	0.350	0.006	0.014	L	0.525	REF	0.021	REF
c	0.080	0.150	0.003	0.006	L1	0.260	0.460	0.010	0.018
D	2.000	2.200	0.079	0.087	θ	0°	8°	0°	8°
E	1.150	1.350	0.045	0.053					

**Notes :** 1.Controlling dimension : millimeters.  
 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.  
 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

**Material :**

- Lead : Pure tin plated.
- Mold Compound : Epoxy resin family, flammability solid burning class:UL94V-0.

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